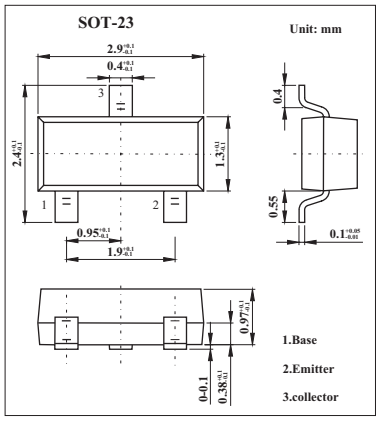
TY Semicondutor®

Product specification

2SC3361



■ Features

- Fast switching speed.
- High breakdown voltage.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Collector current (pulse)	I_{CP}	400	mA
Base current	I_B	40	mA
Collector dissipation	P_C	150	mW
Jumction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

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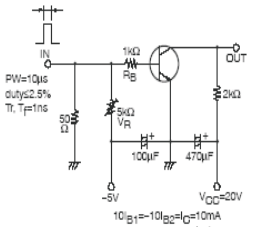
■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 40V , I_E = 0			0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 4V , I_C = 0			0.1	μA
DC current Gain	h_{FE}	V_{CE} = 6V , I_C = 1mA	90		400	
Gain bandwidth product	f_T	V_{CE} = 6V , I_C = 1mA		100		MHz
Common base output capacitance	Cob	V_{CB} = 6V , f = 1MHz		2.7		pF
Collector-to-emitter saturation voltage	$V_{CE(sat)}$	I_C = 10mA , I_B =1mA		0.1	0.4	V
Base-to-emitter saturation voltage	$V_{BE(sat)}$	I_C = 10mA , I_B =1mA		0.75	1.1	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	60			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	50			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	5			V
Delay time	t_d			40		ns
Rise time	t_r			80		ns
Storage time	t_{stg}			230		ns
Fall time	t_f			160		ns

■ hFE Classification

Marking	S4	S5	S6
hFE	90～180	135～270	200～400